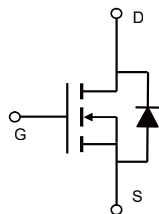


Description

Features ● 100V,59A $R_{DS(ON)} < 20m\Omega @ V_{GS} = 10V$ ● Advanced Trench Technology ● Excellent $R_{DS(ON)}$ and Low Gate Charge ● Lead free product is acquired	Application ● Load Switch ● PWM Application ● Power management <i>100% UIS TESTED!</i> <i>100% ΔV_{ds} TESTED!</i>
 TO-252	 Schematic

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	TUBE (PCS)	Inner BOX (PCS)	Per Carton (PCS)
VSM59N10	VSM59N10-T2	TAPING	TO-252	13inch	2500	25000

Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Symbol	Parameter	Max.	Units
V _{DSS}	Drain-Source Voltage	100	V
V _{GSS}	Gate-Source Voltage	±25	V
I _D	Continuous Drain Current	59	A
	T _C = 100°C	38	A
I _{DM}	Pulsed Drain Current ^{note1}	236	A
E _{AS}	Single Pulsed Avalanche Energy ^{note2}	110	mJ
P _D	Power Dissipation	153	W
	T _C = 25°C		
R _{θJC}	Thermal Resistance, Junction to Case	0.98	°C/W
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +175	°C

Electrical Characteristics (T_C=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	100	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =100V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±25V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	2	3	4	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} =10V, I _D =30A	-	15	20	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1.0MHz	-	5211	-	pF
C _{oss}	Output Capacitance		-	232	-	pF
C _{rss}	Reverse Transfer Capacitance		-	163	-	pF
Q _g	Total Gate Charge	V _{DS} =30V, I _D =30A, V _{GS} =10V	-	87	-	nC
Q _{gs}	Gate-Source Charge		-	27	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	21	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =30V,I _D =2A, R _L =15Ω,R _{GEN} =2.5Ω, V _{GS} =10V	-	18	-	ns
t _r	Turn-on Rise Time		-	8	-	ns
t _{d(off)}	Turn-off Delay Time		-	50	-	ns
t _f	Turn-off Fall Time		-	20	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _s	Maximum Continuous Drain to Source Diode Forward Current		-	-	59	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	236	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _s =59A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	T _J = 25°C I _F =28A,dI/dt=100A/μs	-	32	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	55	-	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: T_J=25°C, V_{DD}=50V, V_G=10V, L=0.5mH, R_G=25Ω, I_{AS}=21A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Performance Characteristics

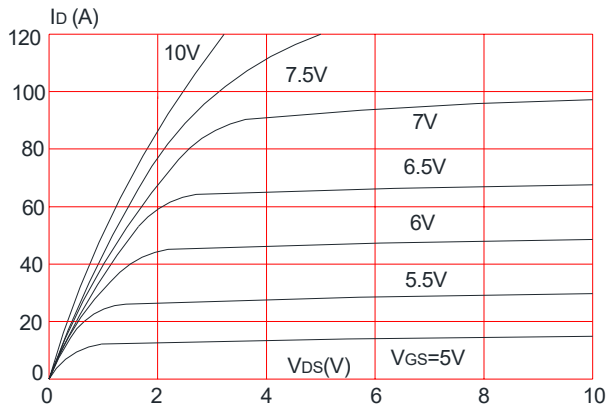
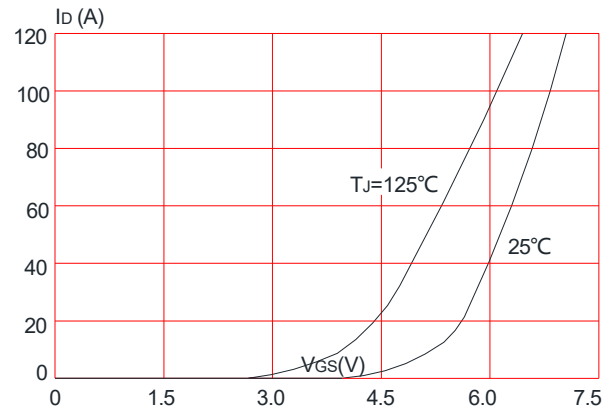
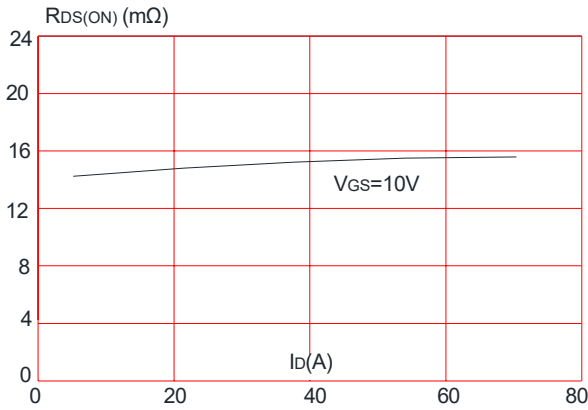
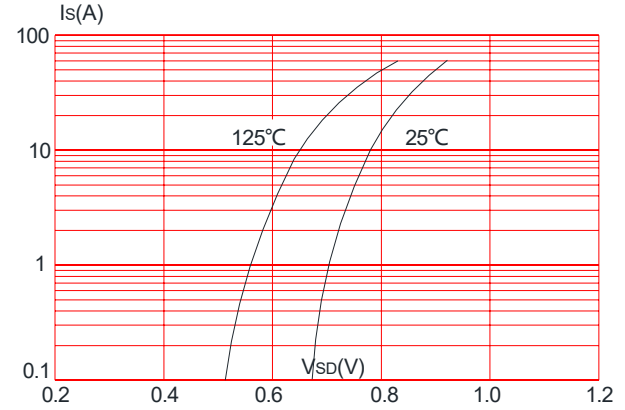
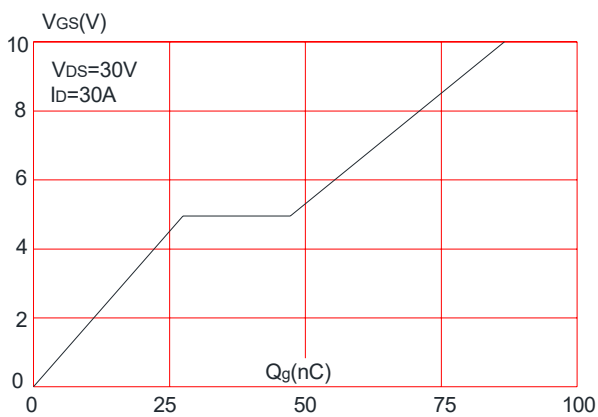
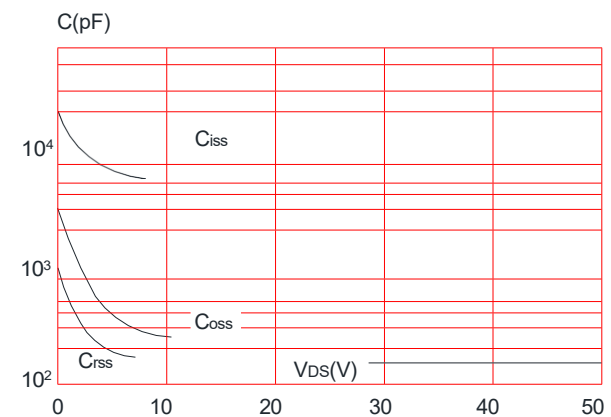
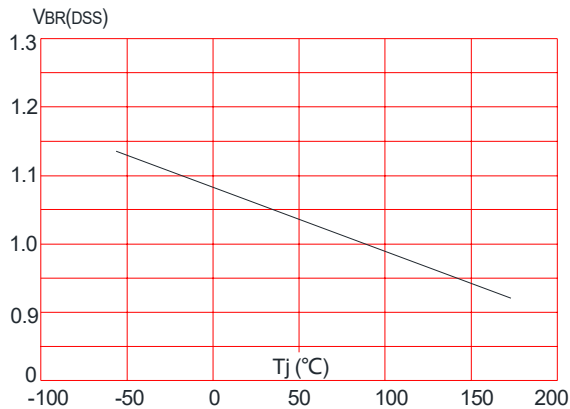
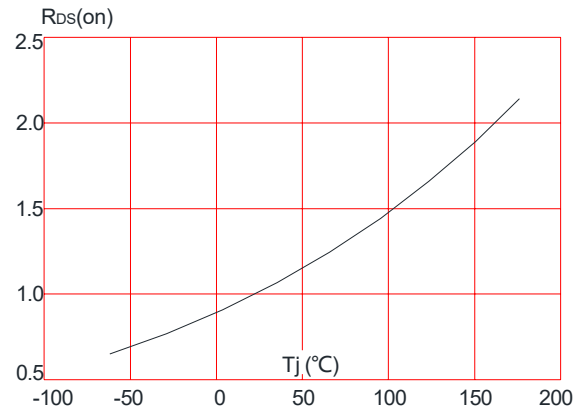
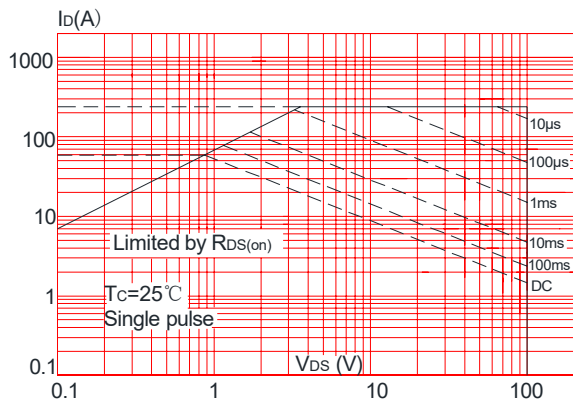
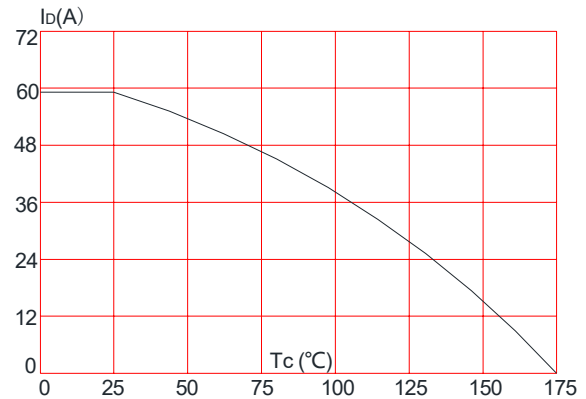
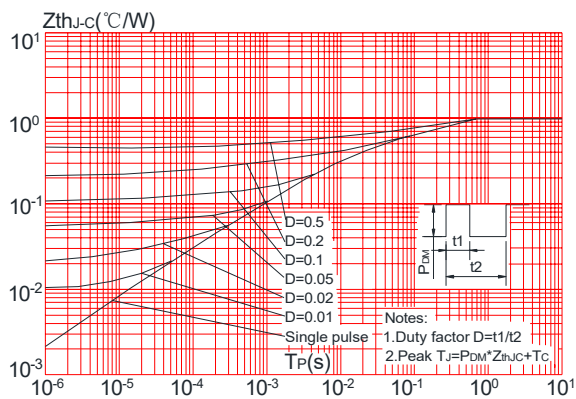
Figure1: Output Characteristics

Figure 2: Typical Transfer Characteristics

Figure 3: On-resistance vs. Drain Current

Figure 4: Body Diode Characteristics

Figure 5: Gate Charge Characteristics

Figure 6: Capacitance Characteristics


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

Figure 8: Normalized on Resistance vs. Junction Temperature

Figure 9: Maximum Safe Operating Area

Figure 10: Maximum Continuous Drain Current vs. Case Temperature

Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case


Test Circuit

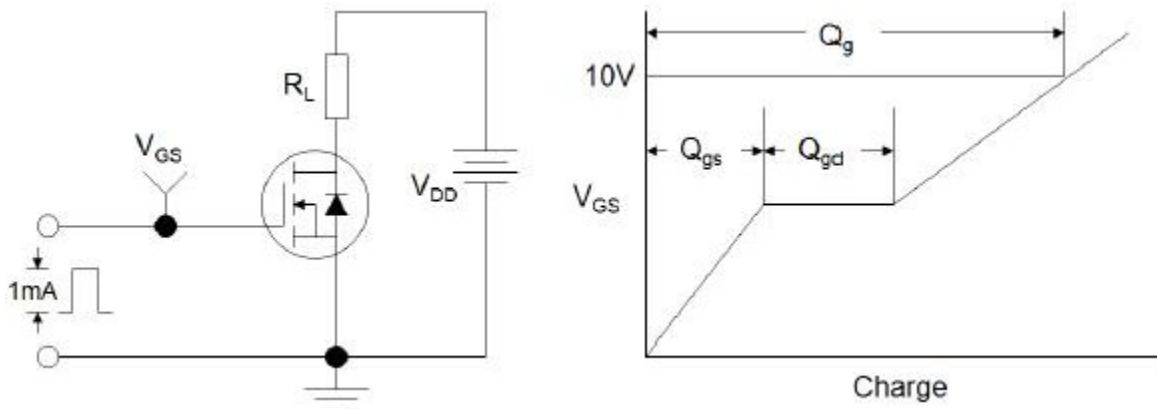


Figure1:Gate Charge Test Circuit & Waveform

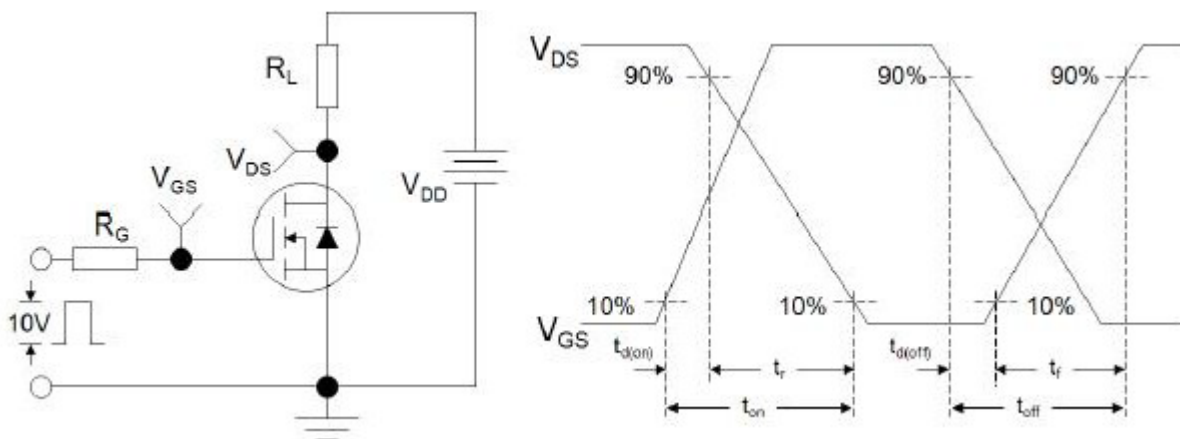


Figure 2: Resistive Switching Test Circuit & Waveforms

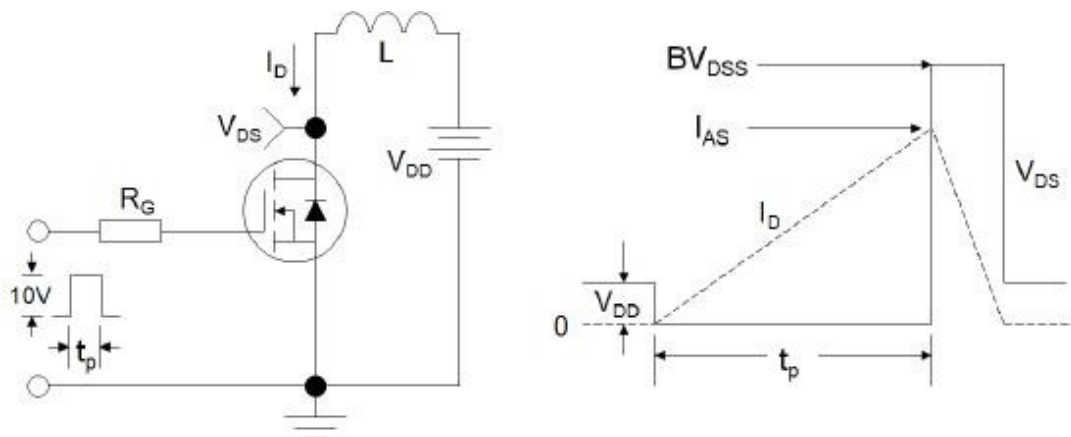


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms